

MegaMOS™ FET

IXTH 35N30
IXTH 40N30
IXTM 40N30

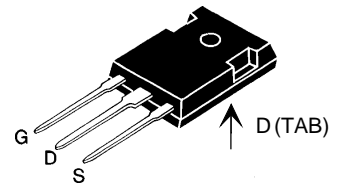
| V_{DSS} | I_{D25} | $R_{DS(on)}$ |
|-----------|-----------|----------------|
| 300 V | 35 A | 0.10 Ω |
| 300 V | 40 A | 0.085 Ω |
| 300 V | 40 A | 0.088 Ω |

N-Channel Enhancement Mode

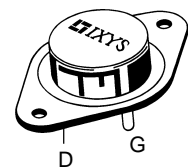


| Symbol | Test Conditions | Maximum Ratings | |
|---|---|-----------------------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 300 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$ | 300 | V |
| V_{GS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 35N30 | 35 A |
| | | 40N30 | 40 A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 35N30 | 140 A |
| | | 40N30 | 160 A |
| P_D | $T_C = 25^\circ\text{C}$ | 300 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| M_d | Mounting torque | 1.13/10 | Nm/lb.in. |
| Weight | | TO-204 = 18 g, TO-247 = 6 g | |
| Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s | | 300 | $^\circ\text{C}$ |

TO-247 AD (IXTH)



TO-204 AE (IXTM)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
 - easy to drive and to protect
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

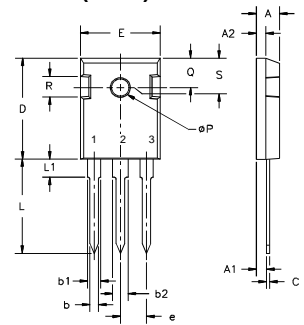
| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|--|---|------|----------------------------------|
| | | min. | typ. | max. |
| V_{DSS} | $V_{GS} = 0\text{ V}$, $I_D = 250\ \mu\text{A}$ | 300 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$ | 2 | | V |
| I_{GSS} | $V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$ | | | $\pm 100\text{ nA}$ |
| I_{DSS} | $V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$ | $T_J = 25^\circ\text{C}$ | | 200 μA |
| | | $T_J = 125^\circ\text{C}$ | | 1 mA |
| $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$, $I_D = 0.5\ I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$ | IXTH35N30 | | 0.10 Ω |
| | | IXTH40N30 IXTM40N30 | | 0.085 Ω 0.088 Ω |

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | | |
|--------------|---|---|------|------|----|
| | | min. | typ. | max. | |
| g_{fs} | $V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test | 22 | 25 | S | |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 4600 | pF | |
| C_{oss} | | | 650 | pF | |
| C_{rss} | | | 240 | pF | |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$, (External) | | 24 | 30 | ns |
| t_r | | | 40 | 90 | ns |
| $t_{d(off)}$ | | | 75 | 100 | ns |
| t_f | | | 40 | 90 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ | | 190 | 220 | nC |
| Q_{gs} | | | 28 | 50 | nC |
| Q_{gd} | | | 85 | 105 | nC |
| R_{thJC} | | | 0.42 | K/W | |
| R_{thCK} | | 0.25 | | K/W | |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|----------|---|---|------|----------------|
| | | min. | typ. | max. |
| I_S | $V_{GS} = 0\text{ V}$ | 35N30 40N30 | | 35 A 40 A |
| I_{SM} | Repetitive; pulse width limited by T_{JM} | 35N30 40N30 | | 140 A 160 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$ | | | 1.5 V |
| t_{rr} | $I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$ | | 400 | ns |

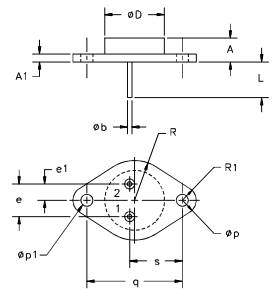
TO-247 AD (IXTH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ØP | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 | BSC | 242 | BSC |

TO-204AE (IXTM) Outline



Pins 1 - Gate 2 - Source
Case - Drain

| Dim. | Millimeter | | Inches | |
|-----------------|------------|-------|--------|------|
| | Min. | Max. | Min. | Max. |
| A | 6.4 | 11.4 | .250 | .450 |
| A ₁ | 1.53 | 3.42 | .060 | .135 |
| Øb | 1.45 | 1.60 | .057 | .063 |
| ØD | | 22.22 | | .875 |
| e | 10.67 | 11.17 | .420 | .440 |
| e ₁ | 5.21 | 5.71 | .205 | .225 |
| L | 11.18 | 12.19 | .440 | .480 |
| Øp | 3.84 | 4.19 | .151 | .165 |
| Øp ₁ | 3.84 | 4.19 | .151 | .165 |
| q | 30.15 | BSC | 1.187 | BSC |
| R | 12.58 | 13.33 | .495 | .525 |
| R ₁ | 3.33 | 4.77 | .131 | .188 |
| s | 16.64 | 17.14 | .655 | .675 |

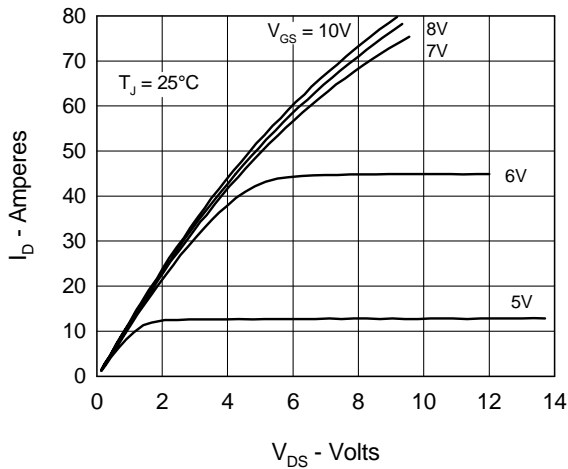
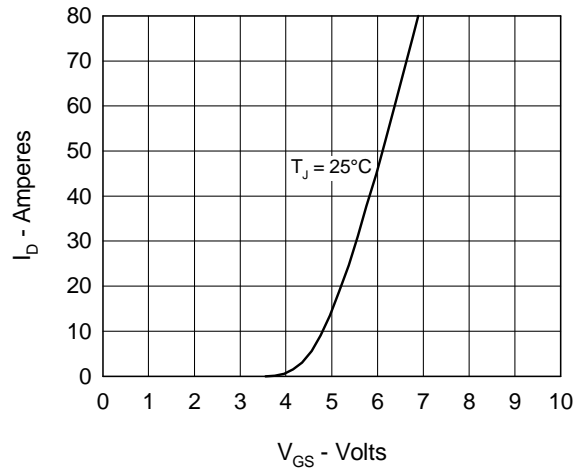
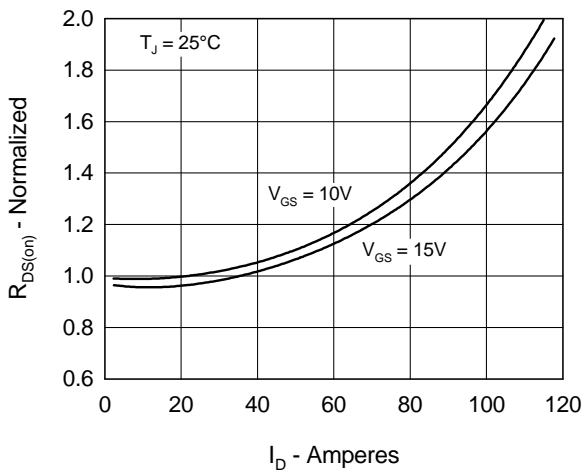
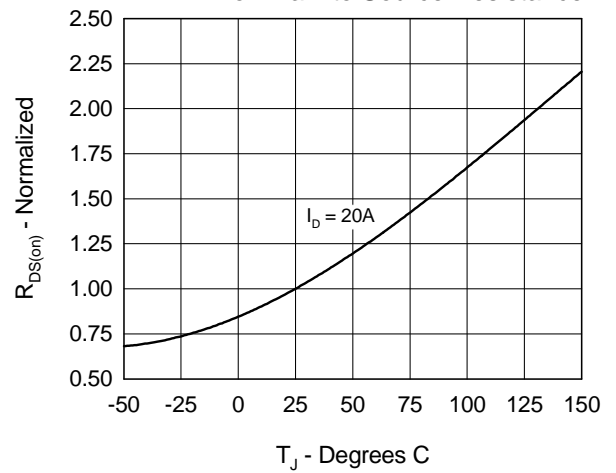
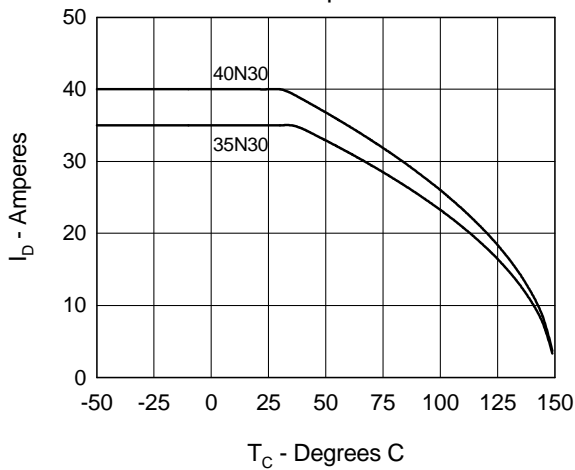
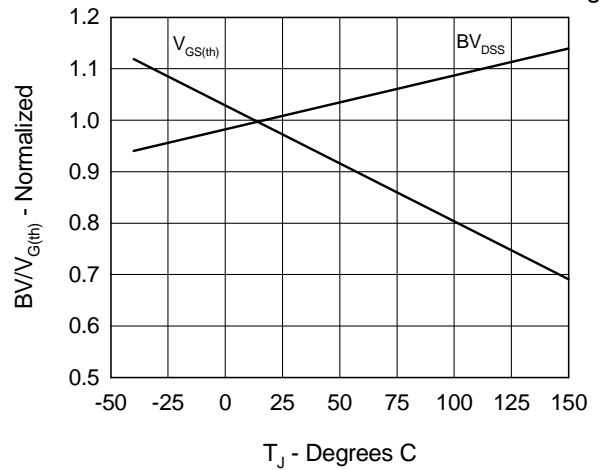
Fig. 1 Output Characteristics

Fig. 2 Input Admittance

Fig. 3 $R_{DS(on)}$ vs. Drain Current

Fig. 4 Temperature Dependence of Drain to Source Resistance

Fig. 5 Drain Current vs. Case Temperature

Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Gate Charge Characteristic Curve

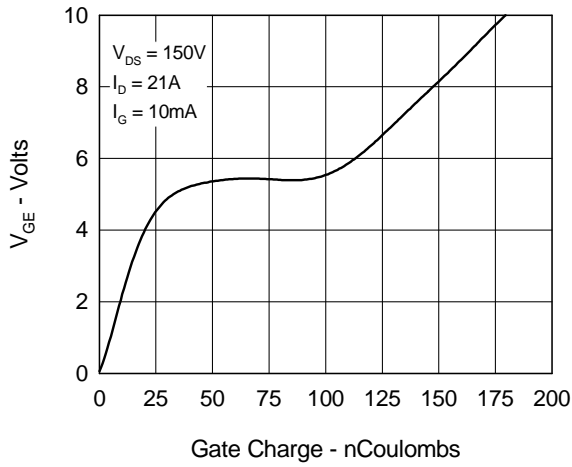


Fig.8 Forward Bias Safe Operating Area

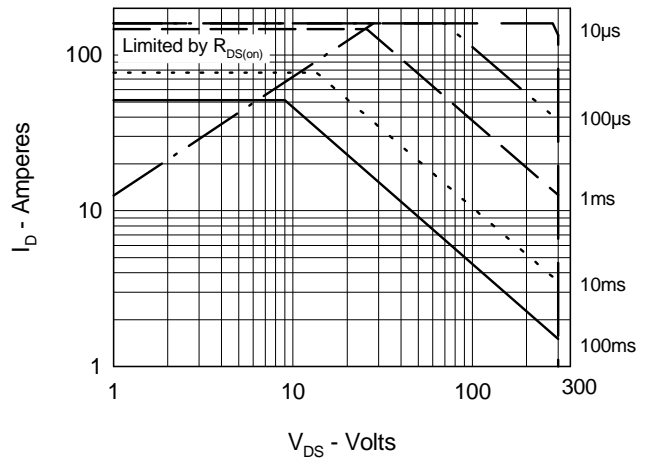


Fig.9 Capacitance Curves

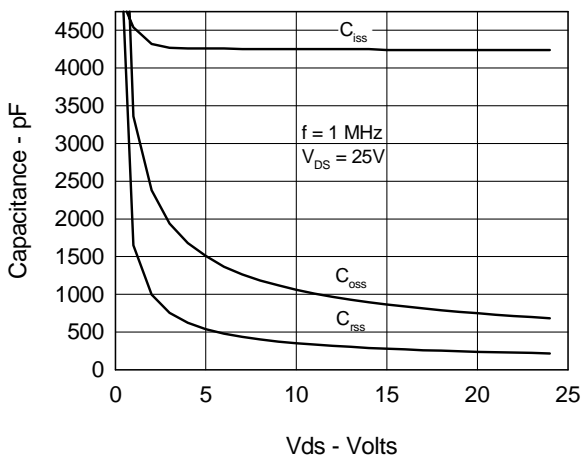


Fig.10 Source Current vs. Source to Drain Voltage

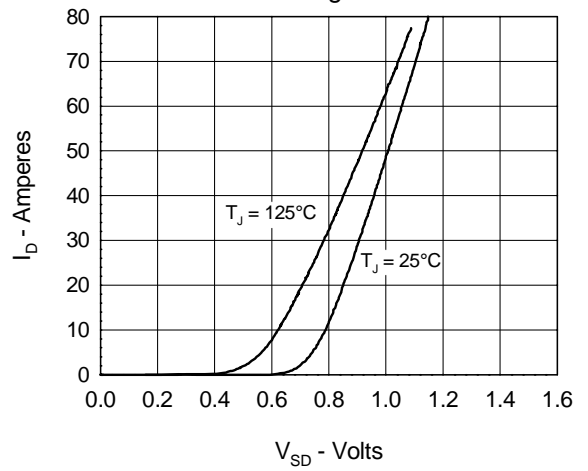


Fig.11 Transient Thermal Impedance

